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(71) Applicant: AGENCY OF IND SCIENCE &

TECHNOL

LTD SHIN ETSU CHEM CO LTD SEIKO INSTR & ELECTRONICS

(72) Inventor: HAYASHI YUTAKA

UMEMURA MITSUO YAMANAKA MITSUYUKI

OKAZAKI SATOSHI KAMIYA MASAAKI TAKADA RYOJI

(74) Representative:

THIN FILM TRANSISTOR (54) MANUFACTURE OF

(57) Abstract:

operation characterized by high PURPOSE: To perform stable by thermal CVD of high-order silane mobility, by using a silicon film made

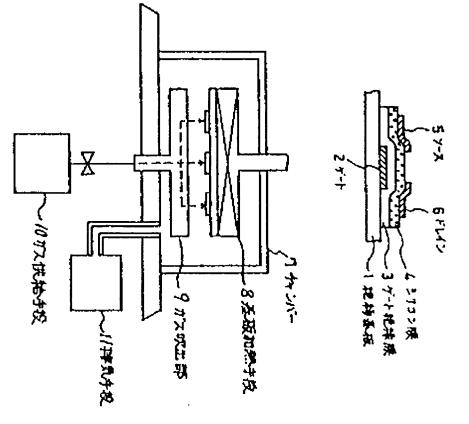
film transistor. channel semiconductor film of a thin such as trisilane or higher as a

thermal decomposition reaction on on the surface of the substrate by a chamber 7; and the film 4 is formed the substrate. the trisilane or higher is introduced in 400°C; the high order silane such as 4 is formed as follows: the substrate and a metal film, are formed. An doublelayer structure of a P-or N-type silicon oxide film and silicon nitride substrate 1, a gate 2 comprising Ni, is heated to a temperature of about low resistance semiconductor film and the like on the gate 2. A silicon evaporation, sputtering and the like. CONSTITUTION: On an insulating transistor is formed. The silicon film inverted staggered type thin film A source 5 and a drain 6, which have thermal CVD method on the film 3. trisilane or higher is formed by a film 4 of high-order silane such as film is laminated by a CVD method A gate insulating film 3 such as a W, Mo and the like is formed by

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